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**INFORMATION DISCLOSURE
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Complete if Known

Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Geusic, Joseph
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 2 of 4

Attorney Docket No: 303.390US4

	US-5,858,877	01/12/1999	Dennison, C. H., et al.	438	700	01/21/1997
<i>for</i>	US-5,897,333	04/27/1999	Goossen, Keith W., et al.	438	455	03/14/1997
<i>for</i>	US-5,900,674	05/04/1999	Wojnarowski, Robert J., et al.	257	774	12/23/1996
<i>for</i>	US-5,901,050	05/04/1999	Imai, Ryuji	361	820	08/21/1997
<i>for</i>	US-5,902,118	05/11/1999	Hubner, Holger	438	106	07/03/1995
<i>for</i>	US-5,903,045	05/11/1999	Bertin, Claude L., et al.	257	621	04/30/1996
<i>for</i>	US-5,915,167	06/22/1999	Leedy, Glenn J.	438	108	04/04/1997
<i>for</i>	US-5,952,665	09/14/1999	Bhargava, R. N.	250	483.1	11/28/1997
<i>for</i>	US-5,963,088	10/05/1999	Czarnul, Z., et al.	330	69	07/29/1997
<i>for</i>	US-6,090,636	07/18/2000	Geusic, Joseph E., et al.	438	31	02/26/1998
<i>for</i>	US-6,122,187	09/19/2001	Ahn, K. Y., et al.	365	63	11/23/1998
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<i>for</i>	JP-04-263462	09/18/1992	Shimizu, Kozo	H01L	25/04	
<i>for</i>	JP-05-145060	06/11/1993	Maaku, Dorainan J.	H01L	29/44	
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<i>for</i>	WO-91/11833	08/08/1991	Madou, Marc J., et al.	H01 R	9/00	
<i>for</i>	WO-94/05039	03/03/1994	Capps, David A., et al.	H01L	23/48	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
<i>for</i>		FORBES, L., et al., "Resonant Forward-Biased Guard-Ring Diodes for Suppression of Substrate Noise in Mixed-Mode CMOS Circuits", <u>Electronics Letters</u> , 31, (April 1995), 720-721	

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Julius J. Halderson

DATE CONSIDERED

6/15/2005

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initials of examiner, inventor or other person to be communicated with. MPEP 2003, Office Procedure Manual. If not in communication with the examiner, include copy of this form with next communication to the examiner. Applicant's unique citation designation number (optional). Applicant is to place a check mark here if English language Translation is checked.

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Filing Date	Even Date Herewith
First Named Inventor	Geusic, Joseph
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 3 of 4

Attorney Docket No: 303.390US4

		FOSTER, R. , et al., "High Rate Low-Temperature Selective Tungsten", In: <u>Tungsten and Other Refractory Metals for VLSI Applications III</u> , V.A. Wells, ed., Materials Res. Soc., Pittsburgh, PA, (1988), 69-72	
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* EXAMINER: Initial of reference considered, whether or not citation is in accordance with MPEP 2103. Items not through citation if not in accordance and not considered. Include copy of this form with each communication to applicant. Applicant's unique citation designation number (optional) Applicant is to place a check mark here if English language translation is checked